

CLAIMS

1. A method for manufacturing semiconductor granules intended to feed a semiconductor material manufacturing melt, characterized in that it comprises a method of sintering and/or melting of powders of at least one material belonging to
5 the group formed by silicon, germanium, gallium arsenide, and the alloys thereof, wherein the granules have a size greater than 1 mm.
2. The method of claim 1, wherein the powders comprise powders of nanometric size.
- 10 3. The method of one of claims 1 and 2, comprising a compaction step followed with a thermal processing step.
4. The method of claim 3, wherein the pressure ranges between 10 MPa and 1 GPa and the temperature is greater than 800°C.
- 15 5. The method of one of claims 1 and 2, comprising a hot pressing step.
6. The method of claim 5, wherein, in the hot pressing step, the pressure is lower than 100 MPa and the temperature is greater than 800°C.
- 20 7. The method of one of claims 1 to 6, comprising a step of placing the powders in a mould (3).
8. The method of one of claims 1 to 7, wherein the powders are doped semiconductor powders.
9. The method of one of claims 1 to 7, comprising a
25 step of anneal or doping of the granules.